Depth profiles and Imaging of impurities on LED epitaxial layers by TOF-SIMS

Accurate depth profiling and imaging analysis can be achieved by using the function of high mass resolution of TOF-SIMS. Furthermore TOF-SIMS enables to acquire depth profiles with good depth resolution and imaging with good spatial resolution as shown below.



The comparison of depth profiles analyzed by 3 different types of SIMS

Accurate Si profile can be obtained by TOF-SIMS with good depth resolution and good detection limit.



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